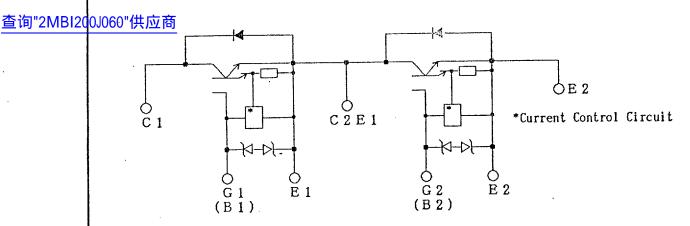


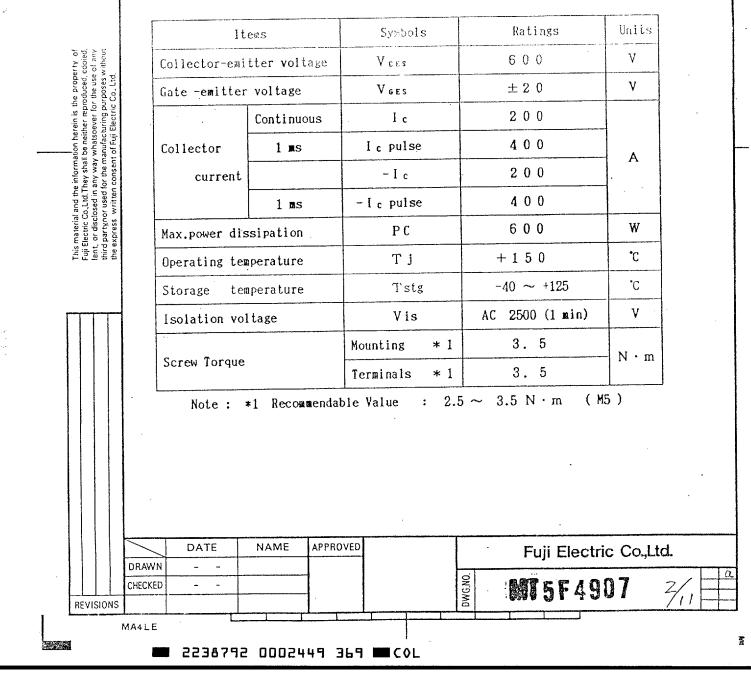
2. Equivalent Circuit

۰,



3. Absolute Maximum Ratings

(Tj=25°C)



ItemsSymbolZero gate voltage collector currentIcesGate-emitter leakage currentIcesGate-emitter thresholdVGE (th)	s min.	typ.	max. 2.0 30	Conditions $Tj = 25^{\circ}C \qquad V_{GE} = 0V \\ V_{CE} = 600V \\ V_{CE} = 0V \\ V_{GE} = \pm 2 0V$	m A m A
collector currentIcesGate-emitterIGESleakage currentIGESGate-emitter thresholdVGE (th)				$Tj=125^{\circ}C$ $V_{CE} = 600V$ $V_{CE} = 0 V$	m A
collector currentGate-emitterleakage currentGate-emitterthresholdVGE (th)				$Tj=125^{\circ}C = 600V$ V <sub>CE</sub> = 0 V	
leakage current Gate-emitter threshold VGE (th)			30		· " Δ
leakage current Gate-emitter threshold V <sub>GE (th)</sub>			30	V -+ 2 OV	
threshold VGE (th)				V GE-IZUV	14
voltage	3.5	5.0	6.5	$V_{CE} = 2 \ 0 \ V$ $I_{C} = 2 \ 0 \ 0 \ MA$	v.
Collector-emitter saturation V <sub>CE (Sat</sub> v Itage	>	1.7	2.5	$V_{GE} = 15V$ I c = 200A	v
5. Dynamic ratings (at Tj =	s min.	typ.	max.	Conditions	Unit
is the preproduction of the preproduction of the properties of the		Characteristics			
of Fuji El		typ.	max.		
E States Input capacitance Cies		12800		$V_{GE} = 0 V$	
Output capacitance Coes				$V_{CE} = 1 0 V$	p l
Input capacitance Cies Unput capacitance Cies Unput capacitance Cies Output capacitance Coes Unput capacitance Coes Number of the manner Reverse transfer capacitance Cres ton ton ton ton				f = 1 MHz	
差達査者 Turn-on time		0.6	1.2	$- V_{cc} = 300V  1_{c} = 200A  V_{cE} = \pm 15V  R_{c} = 9.1\Omega$	μs
tr		0.2	0.6		
Turn-off time		0.8	1.5		
		0.15	0.35	· · ·	

.

6. Characteristics of reverse diode ( at Tj=25°C unless otherwise specified )

## 查询"2MBI200J060"供应商

1.1

11

Items	Symbols	Characteristics			Conditions	Units
		min.	typ.	∎ax.	Conditions	UNITS
Diode forward on-voltage	VF		2.3	3.0	$1 F = 200A$ $V_{GE} = 0V$	v
Reverse recovery time	trr			300	$I F = 200A$ $-di/dt = 600A/\mu s$	ns

## 7. Thermal resistance characteristics

	Items	Symbols	Characteristics			Conditions	Units	
			min.	typ.	xsø.	Condicions	011 05	
This material and the information herein is the property of Fuji Electric Co.Ltd.They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third partynor used for the manufacturing purposes without the express written consent of Fuji Electric CoLtd.	Thermal resistance	Rth(j-c)			0.208	IGBT		
		Rth(j-c)			0.400	Diode	·c / w	
		₩ Rth(c-f)		0.025	-	the base to cooling fin		
e information hey shall be any way who for the manu	X This is th with therm	e value which al compound.	n is defi	ined mour	nting on	the additional cool.	ing fin	
co.Ltd.T Co.Ltd.T closed in nor used								
is materi i Electric it, or disc rd partyr								
the Figure 1								
	DATE N	AME APPROV	'ED			Fuji Electric Co	o.,Ltd.	
	DRAWN CHECKED				DWG.NO.	MT5F4907	4/ a	
REVISIONS		<u>_</u>			Ma G		/11	
MA4LE 2238792 0002451 T17 COL								
		C UUUC451	ו זערו מ					

3

Powered by ICminer.com Electronic-Library Service CopyRight 2003